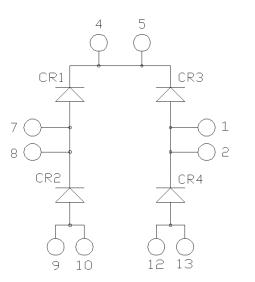
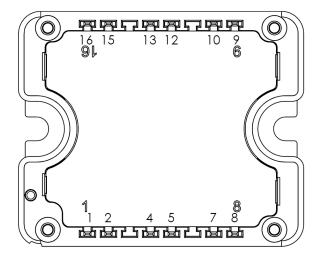


MSCDC50H1201AG SiC Diode Full Bridge Power Module

1 Product Overview

This section shows the product overview for the MSCDC50H1201AG device.





All ratings at T_j = 25°C, unless otherwise specified.

Caution: These devices are sensitive to electrostatic discharge. Proper handling procedures should be followed.



1.1 Features

The following are key features of the MSCDC50H1201AG device:

- Silicon Carbide (SiC) Schottky Diode
 - Zero reverse recovery
 - Zero forward recovery
 - Temperature independent switching behavior
 - Positive temperature coefficient on VF
- High blocking voltage
- Very low stray inductance
- Aluminum nitride (AIN) substrate for improved thermal performance

1.2 Benefits

The following are benefits of the MSCDC50H1201AG device:

- Outstanding performance at high frequency operation
- Solderable terminals for easy PCB mounting
- Direct mounting to heatsink (isolated package)
- Low profile
- RoHS compliant

1.3 Applications

The MSCDC50H1201AG device is designed for the following applications:

- Uninterruptible power supply (UPS)
- Induction heating
- Welding equipment
- High-speed rectifiers



2 Electrical Specifications

This section shows the electrical specifications for the MSCDC50H1201AG device.

2.1 Absolute Maximum Ratings

The following table shows the absolute maximum ratings per SiC diode for the MSCDC50H1201AG device.

Table 1 • Absolute Maximum Ratings

Symbol	Parameter		Maximum Ratings	Unit
VRRM	Repetitive peak reverse voltage		1200	V
lf	DC forward current	Tc = 100 °C	50	А

The following table shows the thermal and package characteristics of the MSCDC50H1201AG.

Table 2 • Thermal and Package Characteristics

Symbol	Characteristic	Min	Max	Unit		
VISOL	RMS isolation voltage, any terminal to case t =1 minute, 50 Hz/60 Hz			4000		V
۲ı	Operating junction temperature range			-40	175	°C
TJOP	Recommended junction temperature under switching conditions				TJmax-25	
Tstg	Storage temperature range			-40	125	
Tc	Operating case temperature			-40	125	
Torque	Mounting torque	To heatsink	M4	2	3	N.m
Wt	Package weight				80	g

2.2 Electrical Performance

The following table shows the electrical characteristics per SiC diode of the MSCDC50H1201AG.

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
VF	Diode forward voltage	IF = 50 A	T _j = 25 °C		1.5	1.8	V
			T _j = 175 °C		2.1		-
Irm	Reverse leakage current	V _R = 1200 V	T _j = 25 °C		15	200	μΑ
			T _j = 175 °C		250		-
Qc	Total capacitive charge	V _R = 600 V			224		nC
С	Total capacitance	f = 1 MHz, V _R = 400 V			246		pF
		f = 1 MHz, V _R = 8	300 V		182		-
RthJC	Junction-to-case thermal resista	ance				0.56	°C/W

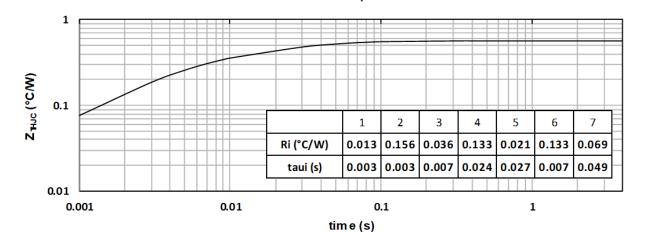
Table 3 • Electrical Characteristics Per Diode



2.3 Performance Curves

Figure 1 • Maximum Transient Thermal Impedance

This section shows the typical performance curves for the MSCDC50H1201AG device.



Maxim um thermal impedance



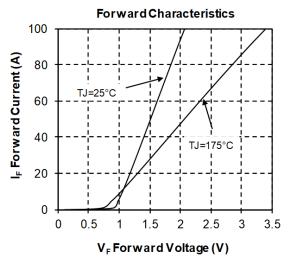
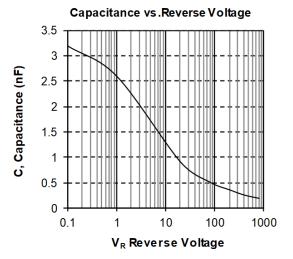


Figure 3 • Capacitance vs. Reverse Voltage





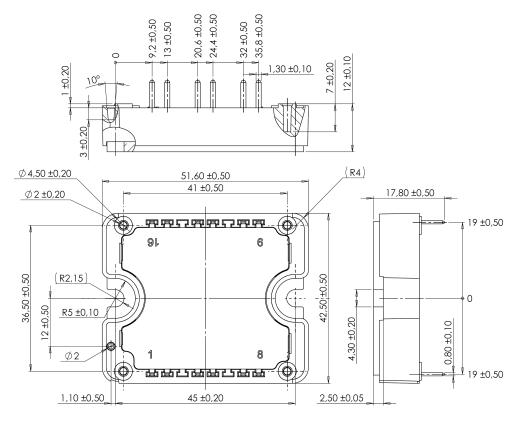
3 Package Specifications

This section shows the package specifications for the MSCDC50H1201AG device.

3.1 Package Outline Drawing

This section shows the package outline drawing of the MSCDC50H1201AG device. The dimensions in the following figure are in millimeters.

Figure 4 • Package Outline Drawing







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